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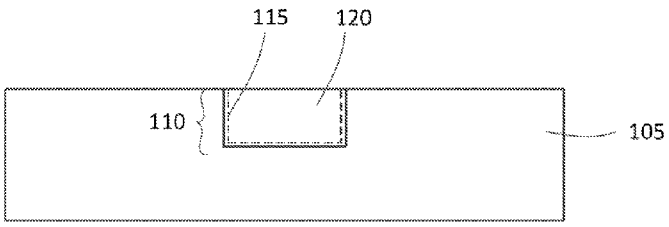


Fig. 1

(57) Abstract: Conducting alloys comprising cobalt, tungsten, and boron and conducting alloys comprising nickel, tungsten, and boron are described. These alloys can, for example, be used to form metal interconnects, can be used as liner layers for traditional copper or copper alloy interconnects, and can act as capping layers. The cobalt-tungsten and nickel tungsten alloys can be deposited using electroless processes.

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